

Notice of References Cited	Application/Control No. 10/710,724		Applicant(s)/Patent Under Reexamination KANG ET AL.	
	Examiner Russell M. Kobert		Art Unit 2829	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-6,326,792	12-2001	Okada, Kenji	324/456
	C	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

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	V	Guoqiao Tao et al, "Fast wafer level monitoring of stress induced leakage current in deep sub-micron embedded non-volatile memory processes," 2002 (Month Unavailable), IEEE, 2002 IRW Final Report, pages 76-78.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.